

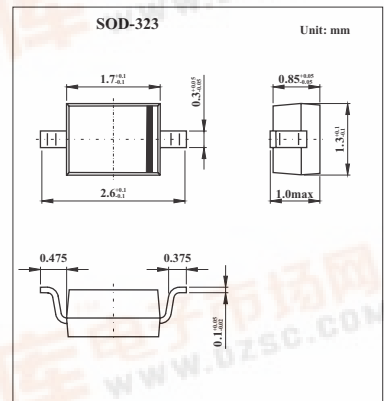
SMD Type Diodes

Silicon Epitaxial Planar Pin Diode

HVU133

■ Features

- Low capacitance.(C=1.0pF max)
- Low forward resistance. (rf=0.7 Ω max)



■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Reverse voltage	V _R	30	V
Power dissipation	P _d	150	mW
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	V _R	I _R = 1 μA	30			V
Reverse current	I _R	V _R = 25 V			100	nA
Forward voltage	V _F	I _F = 2 mA			0.85	V
Capacitance	C ₁	V _R = 1 V, f = 1 MHz			1.0	pF
	C ₆	V _R = 6 V, f = 1 MHz			0.9	
Forward resistance	r _f	I _F = 2 mA, f = 100 MHz		0.55	0.7	Ω

■ Marking

Marking	P3
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